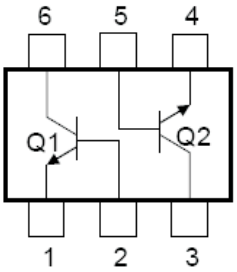
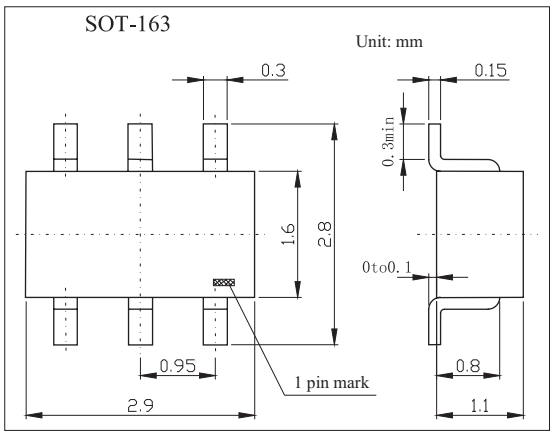
NPN Silicon Epitaxial Transistor

HN1C07F

Features

- Excellent Current Gain(h_{FE})linearity
  :h_{FE}=25(min) at V_{CE}=6V,I_C=400mA





1 Emitter1 **4 Emitter2**
2 Base1 **5 Base2**
3 Collector2 **6 Collector1**

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	500	mA
Base current	I_B	50	mA
power dissipation	P_D	300	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 50V, I_E=0			0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 5V, I_C = 0			0.1	μA
DC current gain *	h_{FE}	V_{CE} = 1V , I_C = 100mA	70		240	
		V_{CE} = 6V , I_C = 400mA	25			
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C = 100mA, I_B = 10mA		0.1	0.25	V
Base emitter voltage *	V_{BE}	V_{CE} = 1V, I_C = 100mA		0.8	1.0	V
Output capacitance	C_{ob}	V_{CE} = 6V, I_E = 0, f = 1MHz		7		pF
Transition frequency	f_T	V_{CE} = 6V, I_E = 20mA		300		MHz

*. PW≤350μs,duty cycle≤2%